

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	450017 2	(etch\$4 or strip\$4 or remov\$4)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/29 18:41
2	BRS	L2	482946	sacrificial or sac or BARC or resist or resists or photoresist or photoresists	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/29 18:41
3	BRS	L3	456650 1	(gap or gaps or opening or openings or hole or holes)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/29 18:41
4	BRS	L4	561539	"hard mask" or "silicon nitride" or SiN or SiON or "silicon oxynitride" or ARC	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/29 18:41
5	BRS	L5	8563	((etch\$4 or strip\$4 or remov\$4)) near8 (sacrificial or sac or BARC or resist or resists or photoresist or photoresists) near8 ("hard mask" or "silicon nitride" or SiN or SiON or "silicon oxynitride" or ARC)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/29 18:41

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L6	2467	((etch\$4 or strip\$4 or remov\$4)) near8 (sacrificial or sac or BARC or resist or resists or photoresist or photoresists) near8 ("hard mask" or "silicon nitride" or SiN or SiON or "silicon oxynitride" or ARC)) same ((gap or gaps or opening or openings or hole or holes))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/29 18:41
7	BRS	L7	391951	plasma	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/29 18:41
8	BRS	L8	486	((((etch\$4 or strip\$4 or remov\$4)) near8 (sacrificial or sac or BARC or resist or resists or photoresist or photoresists) near8 ("hard mask" or "silicon nitride" or SiN or SiON or "silicon oxynitride" or ARC)) same ((gap or gaps or opening or openings or hole or holes))) same plasma	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/29 18:42
9	BRS	L9	219	"CHF.sub.3" near8 (fluorinated hydrocarbon)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/29 18:42

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L10	25	"CHF.sub.3" near8 (fluorinated adj hydrocarbon)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/29 18:42
11	IS&R	L11	1	("5,270,265").PN.	USPAT	2004/06/29 18:42
12	IS&R	L12	1	("6,159,844").PN.	USPAT	2004/06/29 18:42
13	BRS	L13	260	(completely adj (removing or remove or etch or etching or removed or etched)) near4 sacrificial	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/29 18:42

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	4503387	(etch\$4 or strip\$4 or remov\$4)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 09:48
2	BRS	L2	483525	sacrificial or sac or BARC or resist or resists or photoresist or photoresists	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 09:48
3	BRS	L3	4568949	(gap or gaps or opening or openings or hole or holes)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 09:48
4	BRS	L4	562133	"hard mask" or "silicon nitride" or SiN or SiON or "silicon oxynitride" or ARC	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 09:48
5	BRS	L5	8582	((etch\$4 or strip\$4 or remov\$4)) near8 (sacrificial or sac or BARC or resist or resists or photoresist or photoresists) near8 ("hard mask" or "silicon nitride" or SiN or SiON or "silicon oxynitride" or ARC)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 09:48

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L6	2477	((etch\$4 or strip\$4 or remov\$4)) near8 (sacrificial or sac or BARC or resist or resists or photoresist or photoresists) near8 ("hard mask" or "silicon nitride" or SiN or SiON or "silicon oxynitride" or ARC)) same ((gap or gaps or opening or openings or hole or holes))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 09:49
7	BRS	L7	392558	plasma	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 09:49
8	BRS	L8	487	((((etch\$4 or strip\$4 or remov\$4)) near8 (sacrificial or sac or BARC or resist or resists or photoresist or photoresists) near8 ("hard mask" or "silicon nitride" or SiN or SiON or "silicon oxynitride" or ARC)) same ((gap or gaps or opening or openings or hole or holes))) same plasma	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 09:49
9	BRS	L9	219	"CHF.sub.3" near8 (fluorinated hydrocarbon)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 09:49

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L10	25	"CHF.sub.3" near8 (fluorinated adj hydrocarbon)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 09:49
11	IS&R	L11	1	("5,270,265").PN.	USPAT	2004/07/01 09:49
12	IS&R	L12	1	("6,159,844").PN.	USPAT	2004/07/01 09:49
13	BRS	L14	262	(completely adj (removing or remove or etch or etching or removed or etched)) near4 sacrificial	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 11:44

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L46	182226	"hard mask" or SiN or "Silicon nitride"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 18:01
2	BRS	L47	24340	sacrificial	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 18:01
3	BRS	L48	147061 1	etch\$4 or strip\$6 or lift-off or (lift adj off)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 18:01
4	BRS	L49	692	(etch\$4 or remov\$6 or strip\$6) near8 sacrificial near8 ("hard mask" or SiN or "silicon nitride" or "silicon oxynitride" or SiON or ARC or antireflect\$6 or anti-reflect\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 18:02
5	BRS	L50	31673	expos\$6 near4 oxide	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 18:02

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L51	190	((etch\$4 or remov\$6 or strip\$6) near8 sacrificial near8 ("hard mask" or SiN or "silicon nitride" or "silicon oxynitride" or SiON or ARC or antireflect\$6 or anti-reflect\$6)) and (expos\$6 near4 oxide)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 18:02
7	BRS	L52	11	sacrificial same gaps same (hard adj mask)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 18:02
8	BRS	L53	40	single adj plasma adj etch\$4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 18:02
9	BRS	L54	4	(plasma adj etch\$4) with sacrificial with ("hard mask" or SiN or "silicon nitride") with (opening\$3 or gap\$3 or hole\$4 or trench\$4 or spac\$3)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 18:02
10	BRS	L55	472	(etch\$4 or strip\$6 or lift-off or (lift adj off)) near8 sacrificial near8 ("hard mask" or SiN or "Silicon nitride")	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 18:02
11	IS&R	L56	1	("6159821").PN.	USPAT	2004/07/07 18:02

	Type	L #	Hits	Search Text	DBs	Time Stamp
12	BRS	L57	12	("4389294" "4692992" "5229316" "5433794" "5712185" "5731241" "5930645" "5940717" "5994201" "5998278" "6001706" "6043133") .PN.	USPAT	2004/07/07 18:02
13	BRS	L58	112	(((etch\$4 or remov\$6 or strip\$6) near8 sacrificial near8 ("hard mask" or SiN or "silicon nitride" or "silicon oxynitride" or SiON or ARC or antireflect\$6 or anti-reflect\$6)) and (expos\$6 near4 oxide)) and plasma	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 18:02
14	BRS	L59	1	(one near2 plasma near2 etch\$6) near8 sacrificial near8 "hard mask"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 18:02
15	BRS	L60	256	single near2 plasma near2 etch\$4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 18:02
16	IS&R	L61	3622	(438/694) .CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 18:03

	Type	L #	Hits	Search Text	DBs	Time Stamp
17	IS&R	L67	339	(438/695) .CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 18:14
18	IS&R	L68	362	(438/697) .CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 18:41
19	IS&R	L69	133	(438/709) .CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 19:13
20	IS&R	L70	239	(438/717) .CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 19:25
21	IS&R	L71	499	(438/738) .CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/07 19:44